

描述 / Descriptions

SOP-8 塑封封装 P 沟道 MOS 场效应管。

P-Channel Enhancement Mode Field Effect Transistor in a SOP-8 Plastic Package.

特征 / Features

$V_{DS}(V)=-30V$ $I_D=-5.0A$

$R_{DS(ON)} < 65m\Omega (V_{GS}=-10V)$

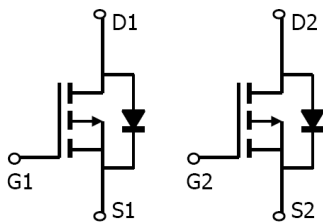
$R_{DS(ON)} < 75m\Omega (V_{GS}=-4.5V)$

用途 / Applications

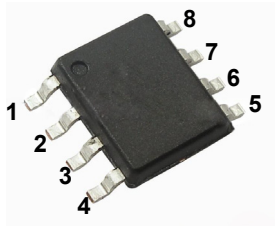
用于电源管理，便携式设备和电池供电系统。适用于作负载开关或脉宽调制应用。

Power Management in Notebook computer, Portable Equipment and Battery powered systems and this device is suitable for use as a load switch or in PWM applications.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1 : S2 PIN 2 : G2 PIN 3 : S1 PIN 4 : G1
PIN 5 : D1 PIN 6 : D1 PIN 7 : D2 PIN 8 : D2

印章代码 / Marking

见印章说明 See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ^A	$I_D (T_a=25^\circ\text{C})$	-5.0	A
	$I_D (T_a=70^\circ\text{C})$	-4.2	A
Pulsed Drain Current ^B	I_{DM}	-20	A
Power Dissipation for Single Operation ^A	$P_D (T_a=25^\circ\text{C})$	2.0	W
	$P_D (T_a=70^\circ\text{C})$	1.4	W
Junction and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150	°C
Thermal Resistance-Junction to Ambient ^A	$R_{\theta JA} (t \leq 10s)$	62.5	°C/W
	$R_{\theta JA}$	110	°C/W
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	40	°C/W

Note:

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10s$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

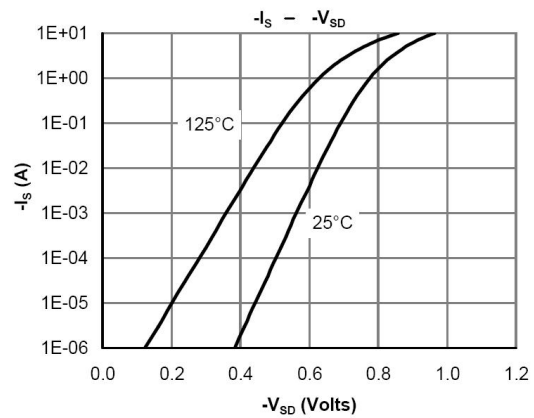
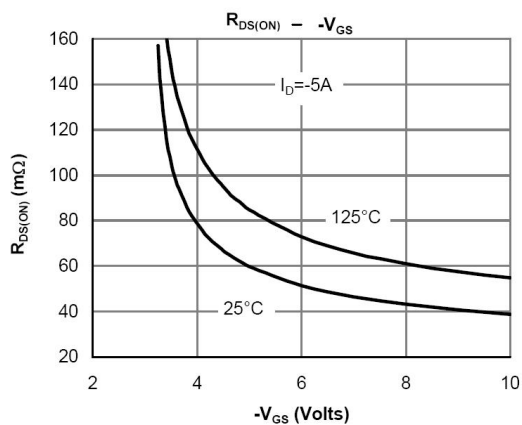
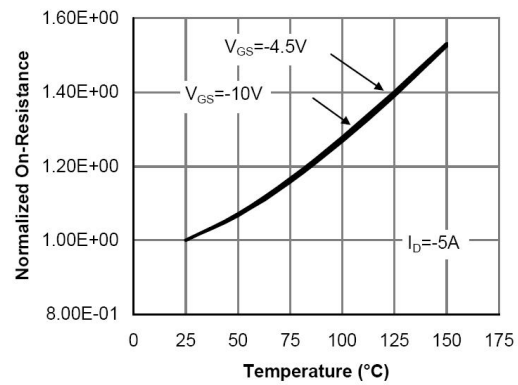
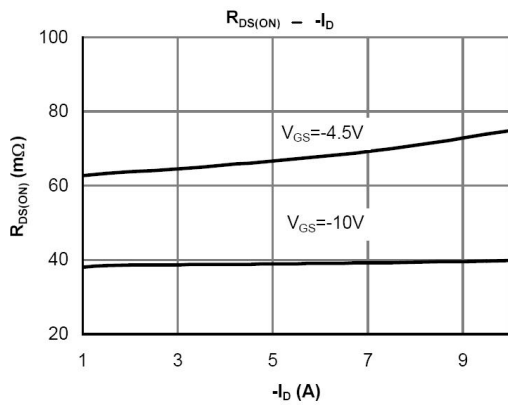
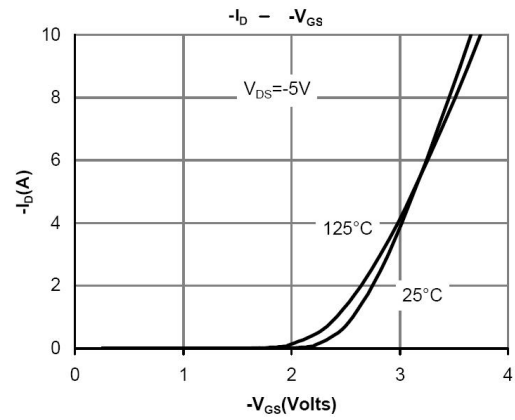
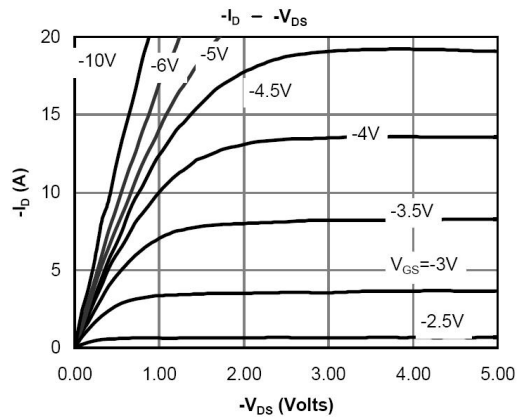
D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

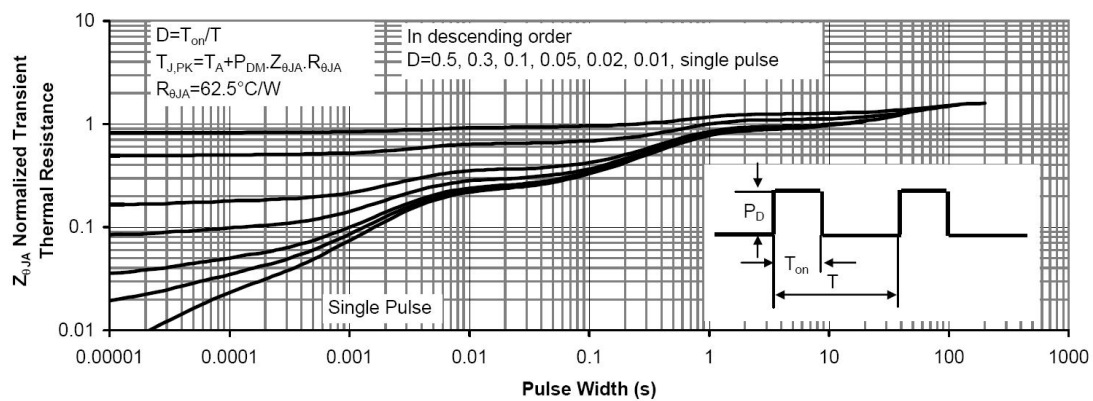
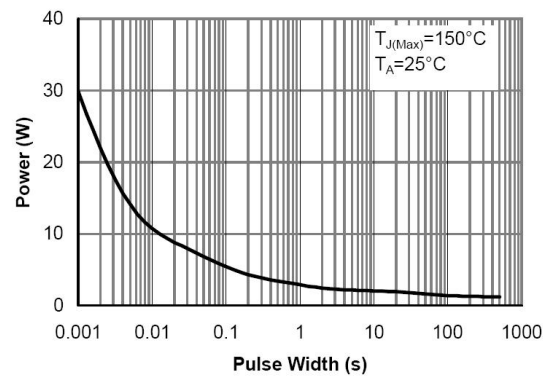
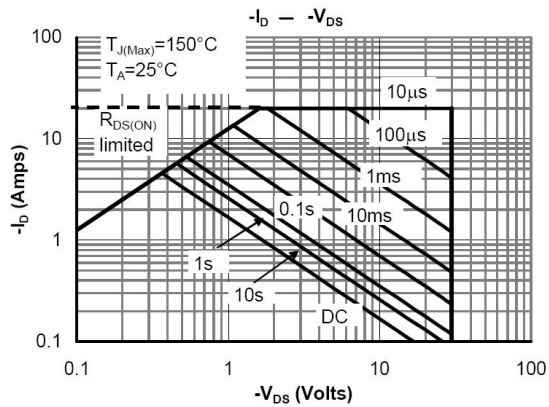
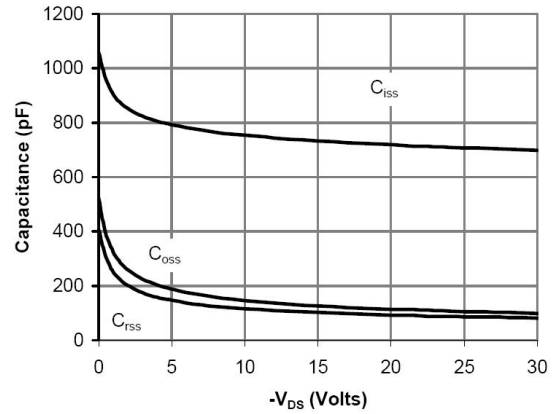
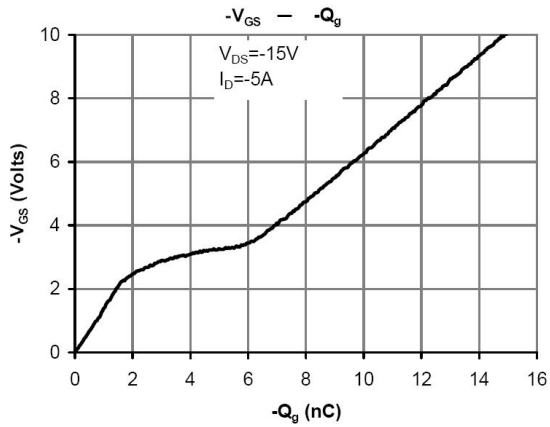
电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=-250\mu A$ $V_{GS}=0V$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-24V$ $V_{GS}=0V$			-1.0	μA
		$V_{DS}=-24V$ $V_{GS}=0V$ $T_J=55^\circ C$			-5.0	
Gate-Body leakage current	I_{GSS}	$V_{DS}=0V$ $V_{GS}=\pm 12V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=-250\mu A$	-0.5	-0.7	-1.3	V
On state drain current	$I_{D(ON)}$	$V_{GS}=-4.5V$ $V_{DS}=-5.0V$	5			A
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-10V$ $I_D=-5.0A$		56	65	m Ω
		$V_{GS}=-10V$ $I_D=-5.0A$ $T_J=125^\circ C$		65	86	
		$V_{GS}=-4.5V$ $I_D=-4.0A$		64	75	
Forward Transconductance	g_{FS}	$V_{DS}=-5.0V$ $I_D=-5.0A$		12		S
Diode Forward Voltage	V_{SD}	$I_S=-1.0A$ $V_{GS}=0$		-0.76	-1.0	V
Total Gate Charge(10V)	Q_g	$V_{GS}=-10V$ $V_{DS}=-15V$ $I_D=-5.0A$		14.7		nC
Total Gate Charge(4.5V)				7.6		
Gate-Source Charge	Q_{gs}			2.0		
Gate-Drain Charge	Q_{gd}			3.8		
Gate Resistance	R_g	$V_{GS}=0V$ $V_{DS}=0V$ $f=1MHz$		10		Ω
Input Capacitance	C_{iss}	$V_{GS}=0V$ $V_{DS}=-15V$ $f=1MHz$		700		pF
Output Capacitance	C_{oss}			120		
Reverse Transfer Capacitance	C_{rss}			75		
Turn-on Delay Time	$t_{d(ON)}$	$V_{GS}=-10V$ $V_{DS}=-15V$ $R_L=3.0\Omega$ $R_{GEN}=3.0\Omega$		8.3		ns
Turn-on Rise Time	t_r			5.0		
Turn-off Delay Time	$t_{d(OFF)}$			29		
Turn-off Fall Time	t_f			14		
Body Diode Reverse Recovery Time	t_{rr}	$I_F=-5.0A$ $di/dt=100A/\mu s$		23.5		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F=-5.0A$ $di/dt=100A/\mu s$		13.4		nC

电参数曲线图 / Electrical Characteristic Curve



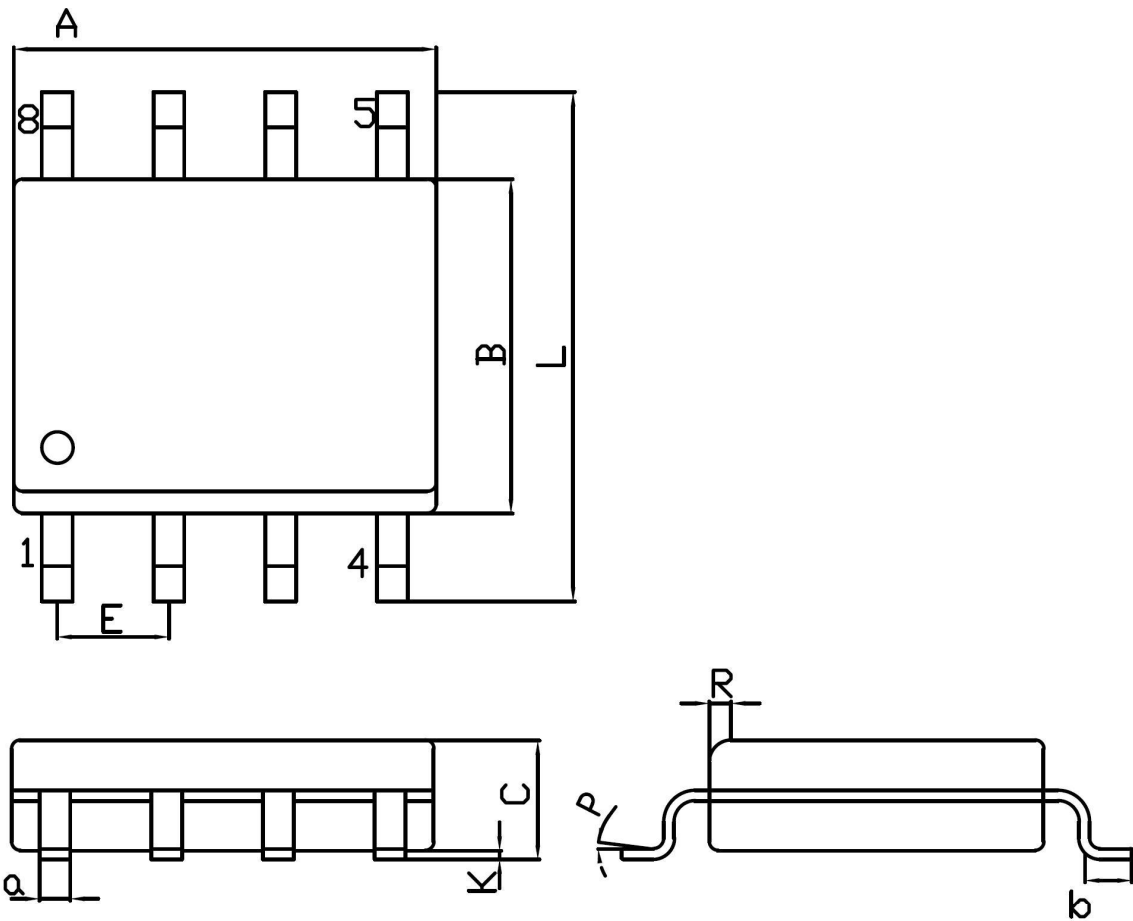
电参数曲线图 / Electrical Characteristic Curve



外形尺寸图 / Package Dimensions

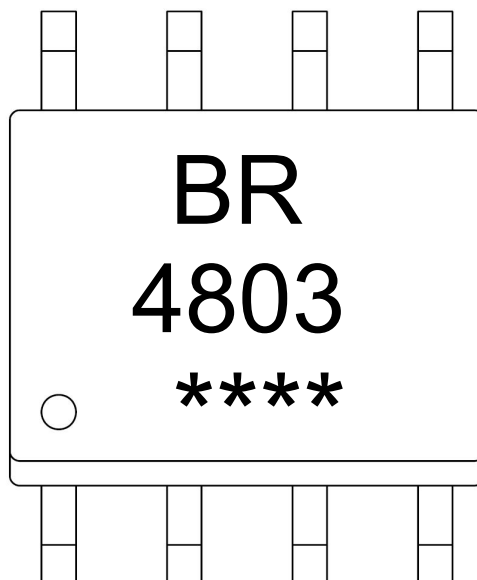
SOP-8

Unit:mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	4.70	5.10	C	1.35	1.75
B	3.70	4.10	a	0.35	0.49
L	5.80	6.20	R	0.30	0.60
E	1.27BSC		P	0°	7°
K	0.12	0.22	b	0.40	1.25

印章说明 / Marking Instructions



说明：

BR： 为公司代码

4803： 为型号代码

****： 为生产批号代码，随生产批号变化。

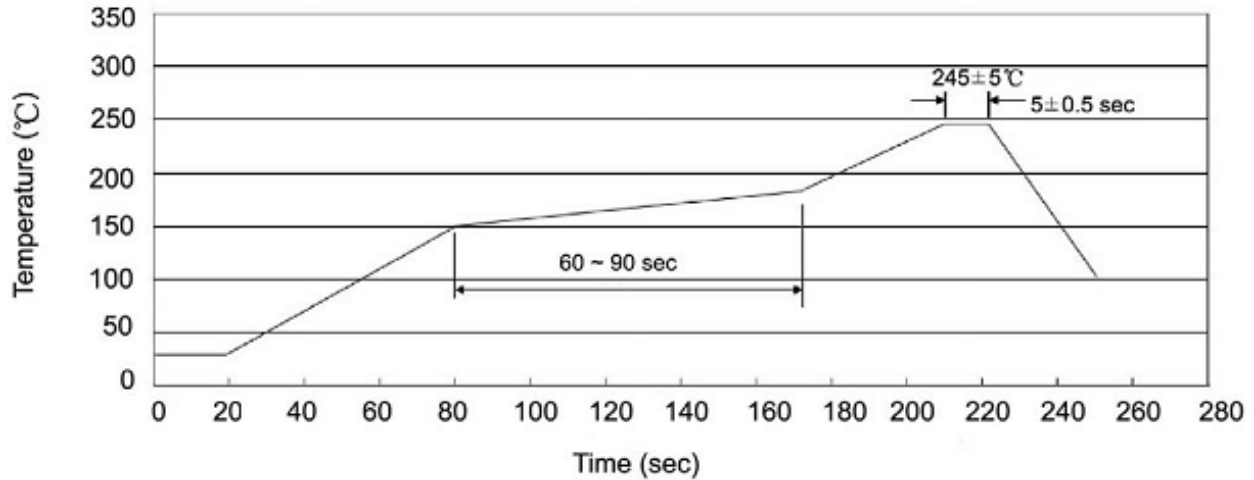
Note:

BR: Company Code.

4803: Product Type

****: Lot No. Code, code change with Lot No.

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150 ~ 180°C，时间 60 ~ 90sec；
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec；
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOP/ESOP-8	4,000	2	8,000	6	48,000	13" ×12	360×360×50	380×335×366

使用说明 / Notices